

# RJK4012DPE

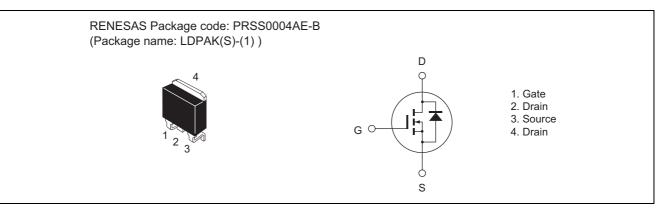
Silicon N Channel MOS FET High Speed Power Switching

> REJ03G1575-0100 Rev.1.00 Aug 08, 2007

# Features

- Low on-resistance
- Low leakage current
- High speed switching

# Outline



# **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ Item Symbol Ratings Unit Drain to source voltage V<sub>DSS</sub> 400 V V Gate to source voltage V<sub>GSS</sub> ±30 15 A Drain current  $I_D$ Note1 Drain peak current 45 A Body-drain diode reverse drain current  $I_{DR}$ 15 A 45 Body-drain diode reverse drain peak current IDR (pulse) А I<sub>AP</sub>Note3 Avalanche current 5 A E<sub>AR</sub><sup>Note3</sup> 1.4 Avalanche energy mJ Pch Note2 W Channel dissipation 100 Channel to case thermal impedance θch-c 1.25 °C/W Channel temperature Tch 150 °C °C Storage temperature Tstg -55 to +150

Notes: 1.  $PW \le 10 \ \mu s$ , duty cycle  $\le 1\%$ 

2. Value at Tc = 25°C

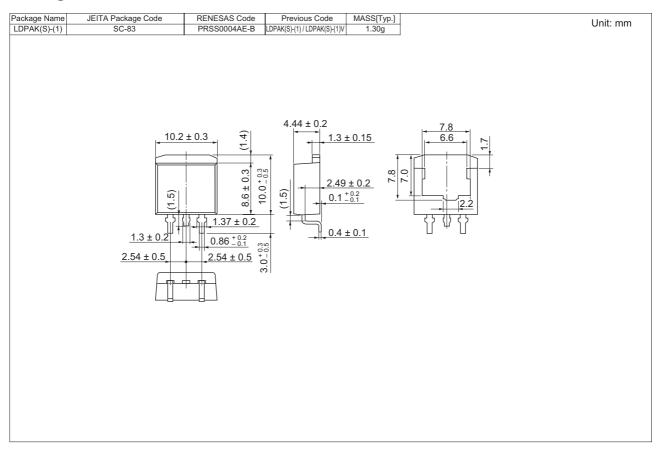
3. STch =  $25^{\circ}$ C, Tch  $\leq 150^{\circ}$ C

# **Electrical Characteristics**

						$(Ta = 25^{\circ}C)$
Item	Symbol	Min	Тур	Мах	Unit	Test conditions
Drain to source breakdown voltage	V <sub>(BR)DSS</sub>	400		—	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Zero gate voltage drain current	I <sub>DSS</sub>	_	—	1	μΑ	$V_{DS} = 400 \text{ V}, V_{GS} = 0$
Gate to source leak current	I <sub>GSS</sub>		—	±0.1	μΑ	$V_{GS} = \pm 30$ V, $V_{DS} = 0$
Gate to source cutoff voltage	V <sub>GS(off)</sub>	3.0	—	4.5	V	$V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$
Static drain to source on state resistance	R <sub>DS(on)</sub>		0.34	0.41	Ω	$I_D = 7.5 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note4}}$
Input capacitance	Ciss	_	1100	_	pF	V <sub>DS</sub> = 25 V
Output capacitance	Coss	_	135	—	pF	V <sub>GS</sub> = 0 f = 1 MHz
Reverse transfer capacitance	Crss		17	_	pF	
Turn-on delay time	t <sub>d(on)</sub>		30	_	ns	I <sub>D</sub> = 7.5 A
Rise time	tr	_	29	—	ns	V <sub>GS</sub> = 10 V
Turn-off delay time	t <sub>d(off)</sub>	_	77	—	ns	R <sub>L</sub> = 26.7 Ω Rg = 10 Ω
Fall time	t <sub>f</sub>	_	19	—	ns	
Total gate charge	Qg		29	—	nC	V <sub>DD</sub> = 320 V
Gate to source charge	Qgs	_	5.5	—	nC	V <sub>GS</sub> = 10 V I <sub>D</sub> = 15 A
Gate to drain charge	Qgd	—	13	—	nC	
Body-drain diode forward voltage	V <sub>DF</sub>	—	0.91	1.55	V	$I_F = 15 \text{ A}, V_{GS} = 0^{Note4}$
Body-drain diode reverse recovery time	t <sub>rr</sub>		260		ns	$I_F = 15 \text{ A}, V_{GS} = 0$ $di_F/dt = 100 \text{ A}/\mu \text{s}$

Notes: 4. Pulse test

# **Package Dimensions**



# **Ordering Information**

Part No.	Quantity	Shipping Container
RJK4012DPE-00-J3	1000 pcs	Taping

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